

--A SEMICONDUCTOR DEVICE HAVING AT LEAST ONE SOURCE/DRAIN REGION FORMED ON AN ISOLATION REGION AND A METHOD OF MANUFACTURE THEREFOR--

**IN THE CLAIMS**

(1) Kindly rewrite Claim 1 as follows:

SUB B1 >

a<sup>1</sup>

1. (Amended) A semiconductor device, comprising:  
a semiconductor substrate;  
a gate formed above the semiconductor substrate;  
an isolation region located within a trench formed in the semiconductor substrate;  
at least a portion of one of a source/drain region formed on the isolation region, but not in the semiconductor substrate.

(2) Kindly rewrite Claim 7 as follows:

SUB B3 >

a<sup>2</sup>

7. (Amended) A semiconductor device, comprising:  
a channel region located in a semiconductor substrate;  
a trench located adjacent a side of the channel region;  
an isolation region located in the trench; and  
at least a portion of one of a source/drain region located on the isolation region, but not in the semiconductor substrate.

(3) Kindly rewrite Claim 12 as follows:

SUB B5 >

a<sup>3</sup>

12. (Amended) A semiconductor device, comprising:

*a<sup>3</sup> could*

~~a channel region located in a semiconductor substrate;~~  
~~an isolation region located adjacent the channel region, the isolation region being located within a trench formed in the semiconductor substrate and not extending under the channel region;~~  
~~and~~  
~~source/drain regions having a first portion located in the semiconductor substrate and a second portion located on the isolation region, but not in the semiconductor substrate.~~

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(4) Kindly rewrite Claim 17 as follows:

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*SUB B6 >*

*a<sup>4</sup>*

~~17. (Amended) A semiconductor device, comprising:~~  
~~a first transistor located adjacent a second transistor, wherein both the first and second transistors are located over a semiconductor substrate;~~  
~~an isolation region located between the first and second transistors and within a trench located within the semiconductor substrate; and~~  
~~source/drain regions associated with each of the first and second transistors, each of the source/drain regions having a first portion located in the semiconductor substrate and a second portion located on the isolation region, but not in the semiconductor substrate.~~

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(5) Kindly rewrite Claim 21 as follows:

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*SUB B7 >*

*a<sup>5</sup>*

~~21. (Amended) A method of manufacturing a semiconductor device, comprising:~~  
~~providing a semiconductor substrate;~~  
~~creating a gate above the semiconductor substrate;~~  
~~forming an isolation region within a trench located in the semiconductor substrate;~~

forming at least a portion of one of a source/drain region above the isolation region, but not in the semiconductor substrate.

*a5  
could*

[6] Kindly rewrite Claim 22 as follows:

22. (Amended) The method as recited in Claim 21 wherein forming an isolation region includes forming an isolation region adjacent to the semiconductor substrate.

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[7] Kindly rewrite Claim 27 as follows:

*SUB B9 >*

27. (Amended) An integrated circuit, comprising:

semiconductor devices, including;

*a6*

a semiconductor substrate;

a gate formed above the semiconductor substrate;

an isolation region located within a trench formed in the semiconductor substrate;

at least a portion of one of a source/drain region formed above the isolation region,

but not in the semiconductor substrate; and

interconnect structures contacting the semiconductor devices.

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✓  
[8] Kindly cancel Claim 33 without prejudice or disclaimer.